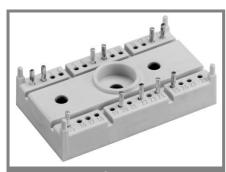
# **SK 70 WT**



# SEMITOP® 3

### **Thyristor**

#### **SK 70 WT**

**Target Data** 

#### **Features**

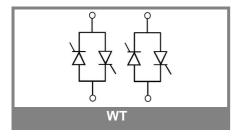
- Compact Design
- · One screw mounting
- Heat transfer and isolation trough direct copper bonded aluminium oxide ceramic (DCB)
- · Glass passived thyristor chips
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

### **Typical Applications**

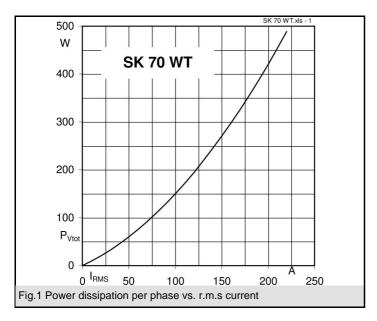
- Soft starters
- Light control (studios, theaters...)
- Temperature control

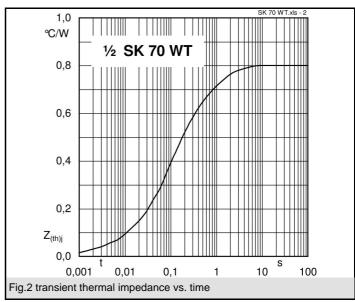
V <sub>RSM</sub> V	V <sub>RRM</sub> , V <sub>DRM</sub> V	I <sub>RMS</sub> = 72 A (T <sub>s</sub> = 85 °C)
900	800	SK 70 WT 08
1300	1200	SK 70 WT 12
1700	1600	SK 70 WT 16

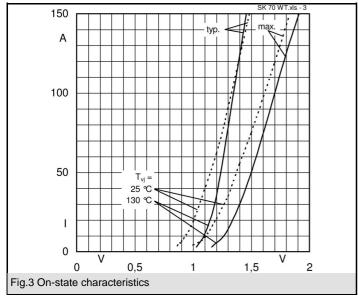
Characteristics Ts = 25°C Unless otherwise specified				
Symbol	Conditions	Values	Units	
I <sub>D</sub>			Α	
$I_{TAV}/I_{FAV}$			Α	
I <sub>RMS</sub>	W1C; sin 180°; per phase at Ts = 85 (100)°C	72 (50)	Α	
I <sub>TSM</sub> /I <sub>FSM</sub>	T <sub>vi</sub> = 25 (125) °C; 10 ms	1000 (900)	Α	
l²t	T <sub>vj</sub> = 25 (125) °C; 8,3 10 ms	5000 (4000)	A²s	
T <sub>stg</sub>		-40 +125	°C	
T <sub>solder</sub>	terminals, 10 s	260	°C	
Thyristor				
(dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	1000	V/µs	
(di/dt) <sub>cr</sub>	$T_{vj}^{'}$ = 125 °C; f = f = 5060 Hz	50	A/µs	
$t_q$	$T_{vj}^{\ \ \ }$ = 125 °C; typ.	80	μs	
I <sub>H</sub>	$T_{vj} = 25 ^{\circ}\text{C}$ ; typ. / max.	100 / 200	mA	
$I_L$	$T_{vj} = 25 \text{ °C}; R_G = 33 \Omega; \text{ typ. / max.}$	200 / 400	mA	
V <sub>T</sub>	$T_{vi} = 25 ^{\circ}\text{C}; (I_T = 120 \text{A}); \text{max}.$	1,8	V	
$V_{T(TO)}$	T <sub>vi</sub> = 125 °C	max. 1	V	
r <sub>T</sub> ′	$T_{vj}^{(j)} = 125  ^{\circ}\text{C}$	max. 6	$m\Omega$	
$I_{DD}$ ; $I_{RD}$	$T_{vj}^{-1}$ = 125 °C; $V_{DD} = V_{DRM}^{-1}$ ; $V_{RD} = V_{RRM}^{-1}$	max. 15	mA	
$R_{th(j-s)}$	per thyristor	0,8	K/W	
$T_{vi}$		- 40 <b>+</b> 125	°C	
$V_{GT}$	$T_{vj}$ = 25 °C; d.c.	2	V	
I <sub>GT</sub>	$T_{vj} = 25 ^{\circ}\text{C}; \text{d.c.}$	100	mA	
$V_{GD}$	$T_{vj} = 125 ^{\circ}\text{C};  \text{d.c.}$	0,25	V	
$I_{GD}$	$T_{vj}$ = 125 °C; d.c.	5	mA	
Diode				
$V_{F}$	$T_{vj} = {^{\circ}C}; (I_F = A); max.$		V	
$V_{(TO)}$	$T_{vj} = {^{\circ}C}$		V	
$r_T$	$T_{vj} = {^{\circ}C}$		mΩ	
$I_{RD}$	$T_{vj} = {^{\circ}C}; V_{RD} = V_{RRM}$		mA	
R <sub>th(j-s)</sub>			K/W	
$T_{vj}$			°C	
Mechanic	al data			
$V_{isol}$	a. c. 50 Hz; r.m.s.; 1 s / 1 min	3000 (2500)	V	
M <sub>1</sub>	mounting torque	2,5	Nm	
w		30	g	
Case	SEMITOP® 3	T 63		

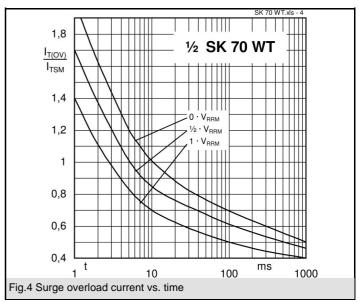


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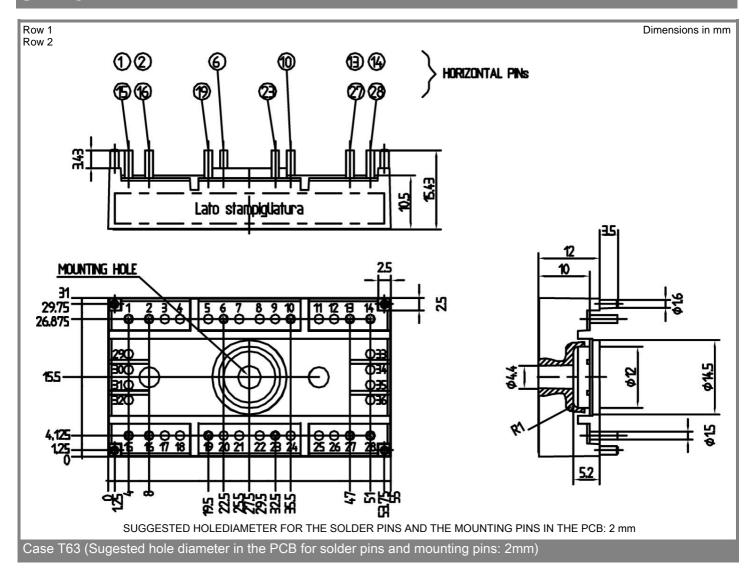


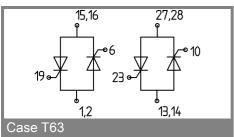






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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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